FOITPE	=== *				OF COMMERCE MARK OFFICE	ATTY. DOCKET I	NO.		SERIAL NO. 09/602,395			
0	LIST OF ART CITED BY APPLICANT  (I) a squared sheets if processory)  APPLICANT John T. Moor											
MAR 2 6 20	om ä	(Use several sheets	if necessary,		FILING DATE June 22, 2000			, GROUP 2812				
U.S. PATENT DOCUMENTS												
*Examiner Initial		Document Number	Date	Name .			Class	Subclass	Filing D If Approp			
758	АА	5,032,545	07/91	Doan et al.		437	242	10/10	190			
789	АВ	5,436,481	07/95	Egawa et al.		257	324	1/19	94			
TOP	AC	5,378,645	01/95	Inoue et al.		437	47	5/19	93			
TSD	AD	5,258,333	11/93	Shappir et al	l.	431	1235	8/19	92			
- CD	AE	5,518,946	05/96	Kuroda		437	52	2/199	74			
(C)	AF	5,445,999	08/95	Thakur et al	<u>.</u>	437	241	11/19	92			
(8)	AG	5,382,533	01/95	Ahmad et al		437	24	119	95			
<u> </u>	AH	5,663,077	09/97	Adachi et al	Adachi et al.			151	9/19	194		
TSP	AI	5,026,574	06/91	Economu et	Economu et al.			248,1	1/198	39		
-CD	, AJ	5,612,558	OTAL:	Harshfield	Harshfield 3.47			298	3/1997			
750	AK	5,719,083	40793	Komatsu	matsu J. ag			¢62	6/10	195		
TST	AL	5,760,475	11/94	Cronin	6.96			728	W1994			
				FOREIGN P.	ATENT DOCUME	NTS						
		Document Number	Date	Country			Class	Subclass	Transla Yes	No No		
TSP	AM	WO 96/39713	12/96	РСТ				·				
	AN		<del> </del>				<del> </del>		-			
ļ	AO		<del>                                     </del>	<del> </del>			<del> </del>		┼──┤			
	AP		<u> </u>				<del> </del>		1			
	AQ	ОТН	PP REFEREI	NCES (includin	Author, Title, D.	ate, Pertinent Pages, I	Etc.)	<u> </u>	J			
BP	AR	Wolf, S., "Silicon	Processing for	the VLSI Era	*, Lattice Press 19	90, Vol. 2, pp. 212-21	3. 	-				
	AS	Wolf, S., "Silicon	9, 194-195, 6	09-614.								
TSP					· · · · · · · · · · · · · · · · · · ·		<del> </del>			-		
	AT	Ko, L. et al., "Th	e Effect of N	litrogen Incorpo	oration into the Ga	te Oxide by Using Sh	allow Implan	tation of Nitr	ogen and Drive	e-In		
Process", IEEE 1996, pp. 32-35.												
EXAMINER			-		DATE CONSID	ERED ((	276	0/				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.												

OTPE				PATE	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET MI22-1384	NO.		SERIAL NO. 09/602,395			
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)								APPLICANT John T. Moore						
MAR 2 6 2001 (Use several sheets if necessary)							FILING DATE June 22, 2000			GROUP 2812				
Te TRADE	MARIT				U.S.	PATENT	DOCUMENTS	_						
*Examiner Initial		Document Date Number				Name			Class	Subclass	Filing Date If Appropriate			
758	AA	5,834	,372	12/95	Lee MCG				438	677	12/1	1995		
158	AB	5,619,	.057	-04796-	Komatsu	ט	4197		257	382	4/1	996		
	AC	5,663,	036	05/97	Seebaue	r-ot-al						<del></del>		
TSP	AD	6,054,	396	04/00	Doan				438	763	9/1	997		
TSP	AE	6,174,	821	01/01	Doan				438	763	GA	997		
758	AF	5,939,	750	08/99	Early .				257	321	1/10	198		
TS	AG	5,254,4	489	10/93.	Nakata			-	437	40	10/1	99/		
TSA	AH	5,464,7	792	11/95	Tseng et al.				437	160	1/1994			
right	AI	5,620,9	908	04/97	Inoh et al.				438	207	9/0	2/995		
751	AJ	5,716,8	364	02/98	Abe				437	43	1/1996			
TSP	AK	5,972,7	783	10/99	Arai et al.			438	513	2/1997				
TSI	AL	6,093,6	6,093,661 07/00			Trivedi et al.			438	769	81899			
	Т	r			FOREIGN	PATEN	T DOCUMENT	s						
		Document Date Number					Country		Class	Subclass	Tran	slation		
	AM										Yes	No		
	AN													
	AO													
	AP					-/-								
	AQ		OTHE	R REFEREN	CES (includi	ing Author	Title Date	Pertinent Pages, Etc.		<u>_</u>	·	L		
	AR													
TIP		Doyle, B. et al., "Simultaneous Growth of Different Thickness Gate Oxides in Silicon CMOS								ng", IEEE V	ol. 16 (7), 1	July 1995,		
	AS	<del>-  </del> ,	pp. 301-302.											
TSP	-		Kuroi, T. et al., "The Effects of Nitrogen Implantation Into P+Poly-Silicon Gate on Gate Oxide Properties", 1994 Sympos. on VLSI											
	<del>                                     </del>		Technology Digest of Technical Papers, IEEE 1994, pp. 107-108.											
TSP	AT Liu, C.T. et al., "Multiple Gate Oxide Thickness for 2GHz System-on-a-Chip Technologies", IEEE 1998, pp. 589-592.													
EXAMINER DATE CONSIDERED 11/27/01														
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.														
considered. In	initial if aclude copy	reterence of this f	considered, wheth orm with next com	er or not citat munication to	ion is in cor applicant.	nformance	with MPEP 60	99; Draw line throug	h citation if	not in confo	ormance and	not		

For FO E				U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET I		SERIAL NO. 09/602,395			
IST OF ART CITED BY APPLICANT							APPLICANT John T. Moore	7 33,000				
MAR 1 6 1001 E							FILING DATE June 22, 2000		GRO 2812	UP		
PAY & TRA	EMART	<del>)</del>	<del> </del>		U.S. PA	TENT DOCUMENTS						
*Examiner Initial		Docu Numl		Date		Name		Class	Subclass	If Appı	Date ropriate	
TSB	`AA	5,994	,749	49 11/99 Oda				257	411	1/10	198	
B	AB	5,674	,788	10/97	Wristers et	al.	437	239	6/19	95		
758	AC	5,596	,218	01/97	Soleimani (	et al.		257	369	10/19	193	
738	AD	5,960	,302	09/99	Ma et al.			433	683	12/1	996	
	AE											
	AF											
	AG											
	АН											
	Al	ļ	·			_				<del>.</del>		
	AJ					· · ·						
	AK					-						
	AL	<u> </u>										
		Docu	ment	Date	FOREIGN 1	PATENT DOCUMEN  Country	TS	Class	Subclass	Trans	lation	
		Numl		<i>D</i> 2.0	County			Class	Jubelass	Yes	No	
	AM						para					
	AN AO		· <u>·</u>									
	AP					/						
	AQ				/							
			ОТНЕ	R REFEREN	CES (includin	ng Author, Title, Date	e, Pertinent Pages, Et	c.)			i	
	AR											
	AS											
	АТ											
EXAMINER	$\leq$	2				DATE CONSIDER	ED \(/6	27/0	1			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.												